

Product Overview

NTMTS0D7N04C: Power MOSFET, Single N-Channel, 40 V, 0.67 mOhms, 420 A

For complete documentation, see the data sheet.

This N-Channel MV MOSFET is produced using ON Semiconductor's advanced Power Trench process that incorporates Shielded Gate technology. This process has been optimized to minimize on-state resistance and yet maintain superior switching performance with best in class soft body diode.

Features

- Small Footprint (8x8 mm)
- Low RDS(on)
- Low QG and Capacitance
- RoHS Compliant

Applications

- Battery Switch
- Switching power supplies
- Load Switch

Benefits

- Compact Design
- Minimize Conduction Losses
- Minimize Driver Losses

End Products

- AC-DC Power Supplies
- Motor Control

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{DSS(BR)} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Package Type	
NTMTS0D7N04CTXG	1.8484	Pb-free Halide free	Active	N-Channel	Single	40	20	4	420	4.9				0.67		140	9230	DFN W-8

For more information please contact your local sales support at www.onsemi.com.

Created on: 6/30/2020